- Wide Supply Voltage Range: 4.5V - 24V
- 4A Peak Source Current and 4A Peak Sink Current
- Flexible Input Logic Positive or Negative Configuration
- TTL Compatible Input Logic Threshold
- Propagation Delay: 13ns
- Typical Rising and Falling Times: 8ns
- Typical Delay Matching: 1ns
- Low Quiescent Current: 65uA
- Output Low When Input Floating
- Independent Enable Logic for Each Channel
- Thermal Shutdown Protection: 170°C
- Available in DFN-8L Package

- IGBT/MOSFET Gate Driver
- Variable Frequency-Drive (VFD)
- Switching Power Supply
- Motor Control
- Solar Power Inverter

The SCT52246 is a wide supply, dual channel, high speed, low side gate drivers for both power MOSFET and IGBT. The SCT52246 features a dual input design which offers flexibility of both inverting (IN pin) and non-inverting (IN+ pin) configuration for each channel. Either IN+ or IN pin controls the state of the driver output. Each channel can source and sink 4A peak current along with rail-to-rail output capability. The 24V power supply rail enhances the driver output ringing endurance during the power device transition.

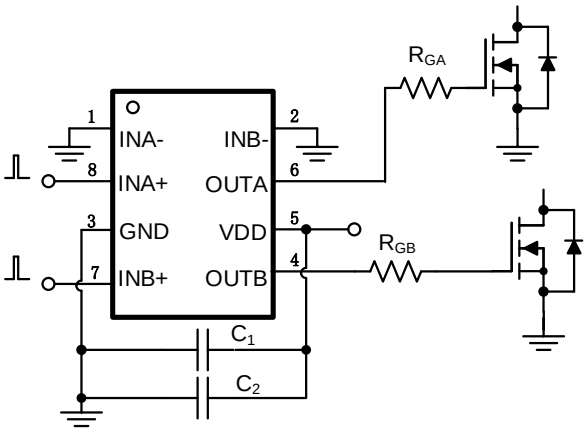
The minimum 13ns input to output propagation delay enables the SCT52246 suitable for high frequency power converter application.

The SCT52246 features wide input hysteresis that is compatible for TTL low voltage logic.

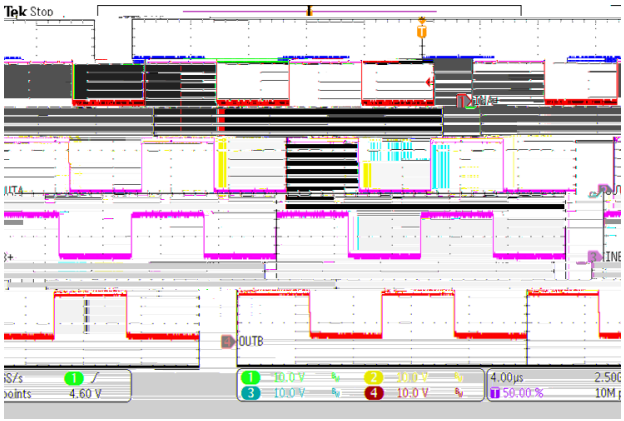
The SCT52246 has very low quiescent current that reduces the stand-by loss in the power converter. The SCT52246 each channel driver adopts non-overlap driver design to avoid the shoot-through of output stage.

The SCT52246 features 170°C thermal shut down. The SCT52246 is available in DFN 3x3-8L package

SCT52246 Typical Application



Application Waveform



NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Revision 1.0：Production

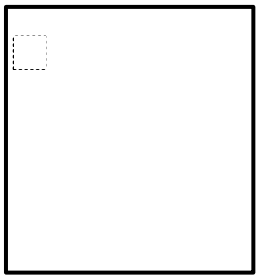
Revision 1.1: Update DEVICE ORDER INFORMATION

ORDERABLE DEVICE	PACKAGING TYPE	STANDARD PACK QTY	PACKAGE MARKING	PINS	PACKAGE DESCRIPTION
SCT52246DTBR	Tape & Reel	5000	2246	8	DFN-8L

Over operating free-air temperature unless otherwise noted(1)

DESCRIPTION	MIN	MAX	UNIT
INA+, INB+	-0.3	26	V
INA-, INB-	-0.3	26	V
OUTA, OUTB	-0.3	26	V
VDD	-0.3	26	V
Operating junction temperature TJ (2)	-40	150	°C
Storage temperature T_{STG}	-65	150	°C

Top View: DFN 3x3 8L Plastic



(1) Stresses beyond those listed under Absolut Maximum Rating may cause device permanent damage. The device is not guaranteed to function outside of its Recommended Operation Conditions.

(2) The IC includes over temperature protection to protect the device during overload conditions. Junction temperature will exceed 150°C when over temperature protection is active. Continuous operation above the specified maximum operating junction temperature will reduce lifetime.

NAME	NO.	PIN FUNCTION
INA-	1	Channel A negative logic input, TTL compatible. Floating logic low.
INB-	2	Channel B negative logic input, TTL compatible. Floating logic low.
GND	3	Power ground. Must be soldered directly to ground plane for thermal performance improvement and electrical contact.
OUTB	4	Channel B gate driver output.
VDD	5	Power Supply, must be locally bypassed by the ceramic cap.
OUTA	6	Channel A gate driver output.
INB+	7	Channel B gate positive logic input, TTL compatible. Floating logic low.
INA+	8	Channel A gate positive logic input, TTL compatible. Floating logic low.

Over operating free-air temperature range unless otherwise noted

PARAMETER	DEFINITION	MIN	MAX	UNIT
V_{DD}	Supply voltage range	4.5	24	V
$V_{INA-,INB-}$	Input voltage range	-0.3	24	V
$V_{INA+,INB+}$	Input voltage range	-0.3	24	V
T_J	Operating junction temperature	-40	150	°C

PARAMETER	DEFINITION	MIN	MAX	UNIT
V_{ESD}	Human Body Model (HBM), per ANSI-JEDEC-JS-001-2014 specification, all pins (1)	-2	+2	kV
	Charged Device Model (CDM), per ANSI-JEDEC-JS-002-2014specification, all pins (1)	-0.5	+0.5	kV

(1) HBM and CDM stressing are done in accordance with the ANSI/ESDA/JEDEC JS-001-2014 specification

PARAMETER	THERMAL METRIC	DFN-8L	UNIT
R	Junction to ambient thermal resistance (1)	46.7	°C/W
R (top)	Junction to case (top) thermal resistance (1)	46.7	
R (bot)	Junction to case (bottom) thermal resistance (1)	9.5	

(1) SCT provides R and R numbers only as reference to estimate junction temperatures of the devices. R and R are not a characteristic of package itself, but of many other system level characteristics such as the design and layout of the printed circuit board (PCB) on which the SCT52246 is mounted, and external environmental factors. The PCB board is a heat sink that is soldered to the leads and thermal pad of the SCT52246. Changing the design or configuration of the PCB board changes the efficiency of the heat sink and therefore the actual R and R .

V_{DD}=12V, T_J=-40°C~150°C, typical values are tested under 25°C.

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
Power Supply and Output						
V_{DD}	Operating supply voltage		4.5		24	V
V_{DD_UVLO}	Input UVLO Hysteresis	V_{DD} rising		4.2 300	4.5	V mV
I_Q	Supply current	V_{DD}=3.5V, INA+ =INB+ =GND, INA-=INB-=GND		65		uA
		V_{DD}=12V, INA+ =INB+ = V_{DD}=12V, INA-=INB-=GND		280		uA
INPUTS						
$V_{INA-,INB-\_H}$	Input logic high threshold Output logic low			2.1	2.4	V
$V_{INA-,INB-\_L}$	Input logic low threshold Output logic high		0.8	1		V
V_{IN-_Hys}	Hysteresis			1.1		V
$V_{INA+,INB+\_H}$	Input logic high threshold			2.1	2.4	V
$V_{INA+,INB+\_L}$	Input logic low threshold		0.8	1		V
V_{IN+_Hys}	Hysteresis			1.1		V
OUTPUTS						
$V_{DD}\_V_{OH}$	Output output high voltage	I_{OUT}= - 10mA			150	mV
V_{OL}	Output low voltage	I_{OUT}= 10mA			10	mV
$I_{SINK/SRC}$	Output sink/source peak current	C_{Load}=10nF, F_{SW}=1kHz		4		A
R_{OH}	Output pull high resistance (only PMOS ON)	I_{OUT}= - 10mA	5	9	18	
R_{OL}	Output pull low resistance	I_{OUT}= 10mA	0.3	0.6	1.2	
Timing						
T_R	Output rising time	C_{Load}=1nF		8	20	ns
T_F	Output falling time	C_{Load}=1nF		8	20	ns
T_{D_IN}	Input to output propagation delay, Rising edge			13	25	ns
	Input to output propagation delay, Falling edge			13	25	ns
T_{M_IN}	Input to output delay matching			1	4	ns
T_{MIN_ON}	Minimum input pulse width	C_{Load}=1nF		20	30	ns
Protection						
T_{SD}	Thermal shutdown threshold*	T_J rising		170		°C
	Hysteresis			25		°C

*Derived from bench characterization

V_{IN}=12V, T_A= 25°C.

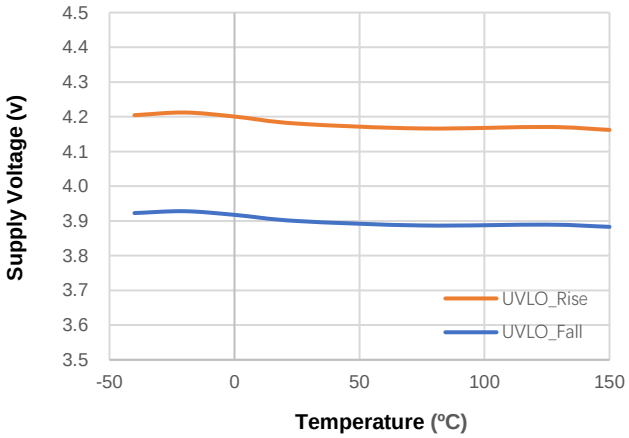


Figure 1. UVLO vs Temperature

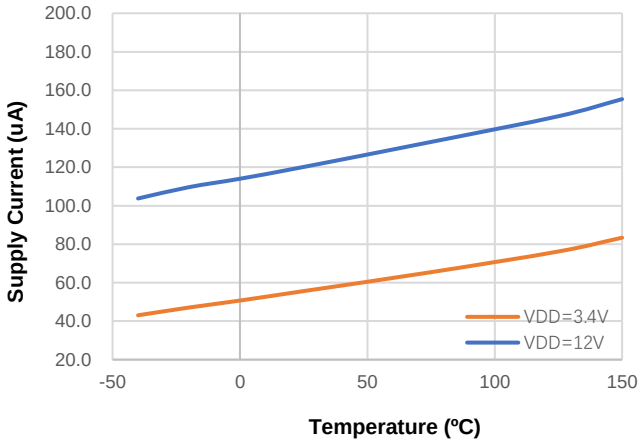


Figure 2. Start-up current vs Temperature

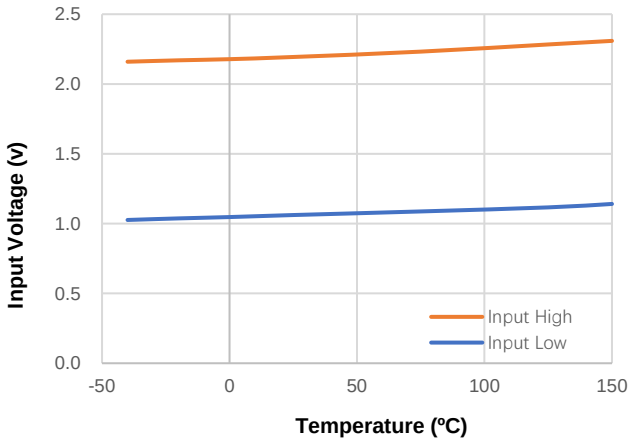


Figure 3. INA+ and INB+ Threshold vs Temperature

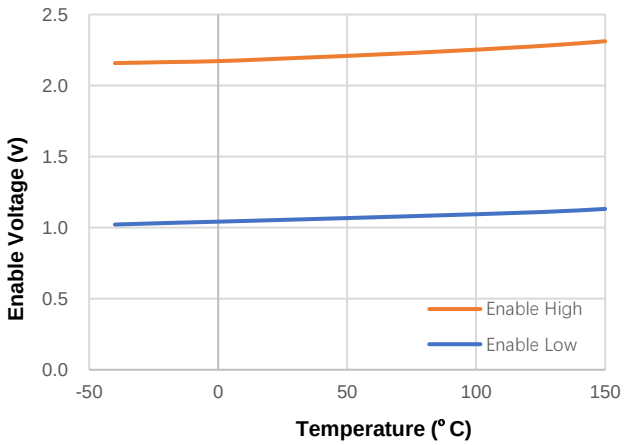


Figure 4. INA- and INB- Threshold vs Temperature

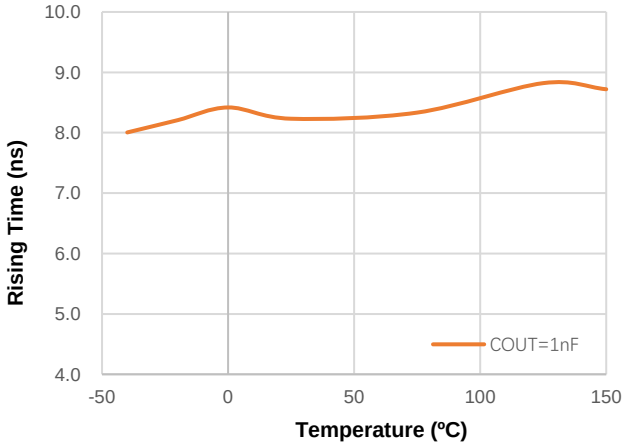


Figure 5 Output Rising Time vs Temperature

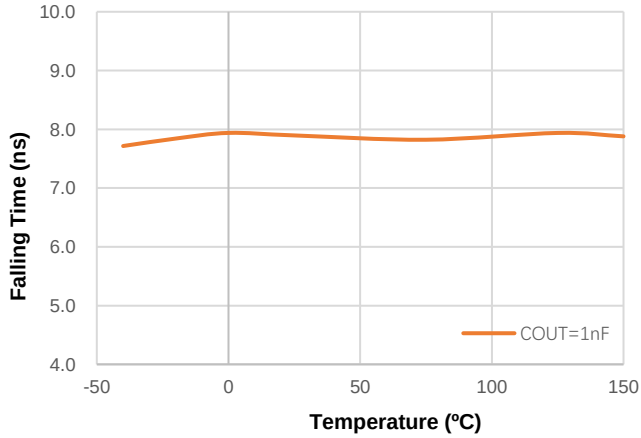


Figure 6. Output Falling Time vs Temperature

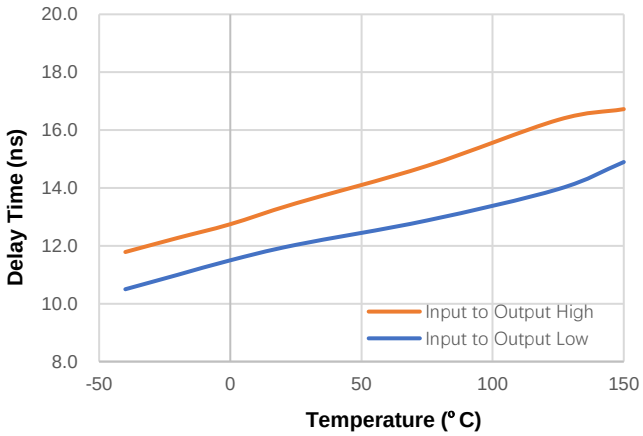


Figure 7. Input to Output Propagation Delay vs Temperature

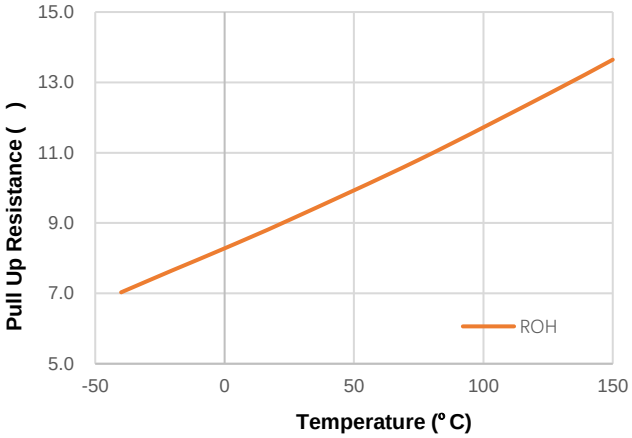


Figure 8. ROH vs Temperature

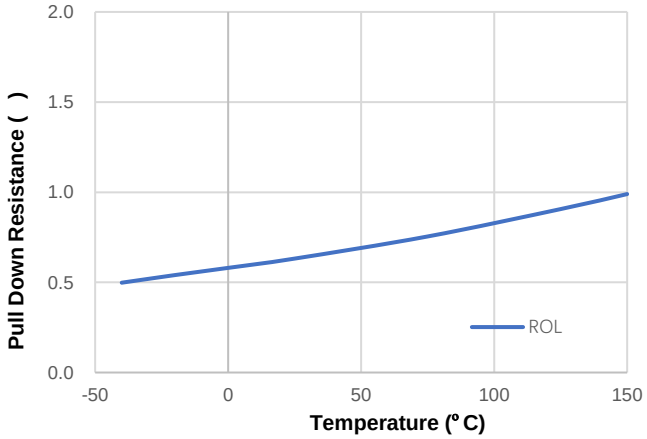


Figure 9. ROL vs Temperature

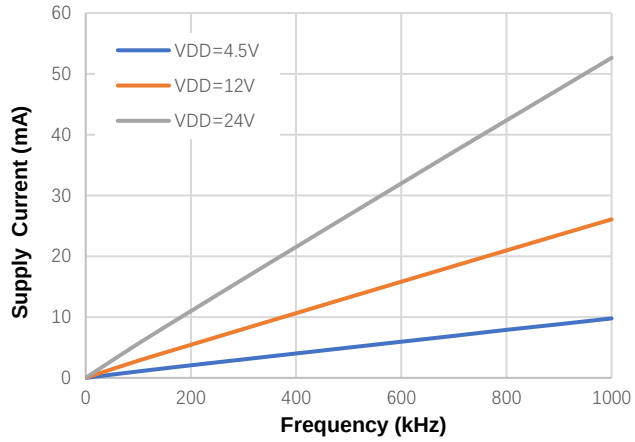
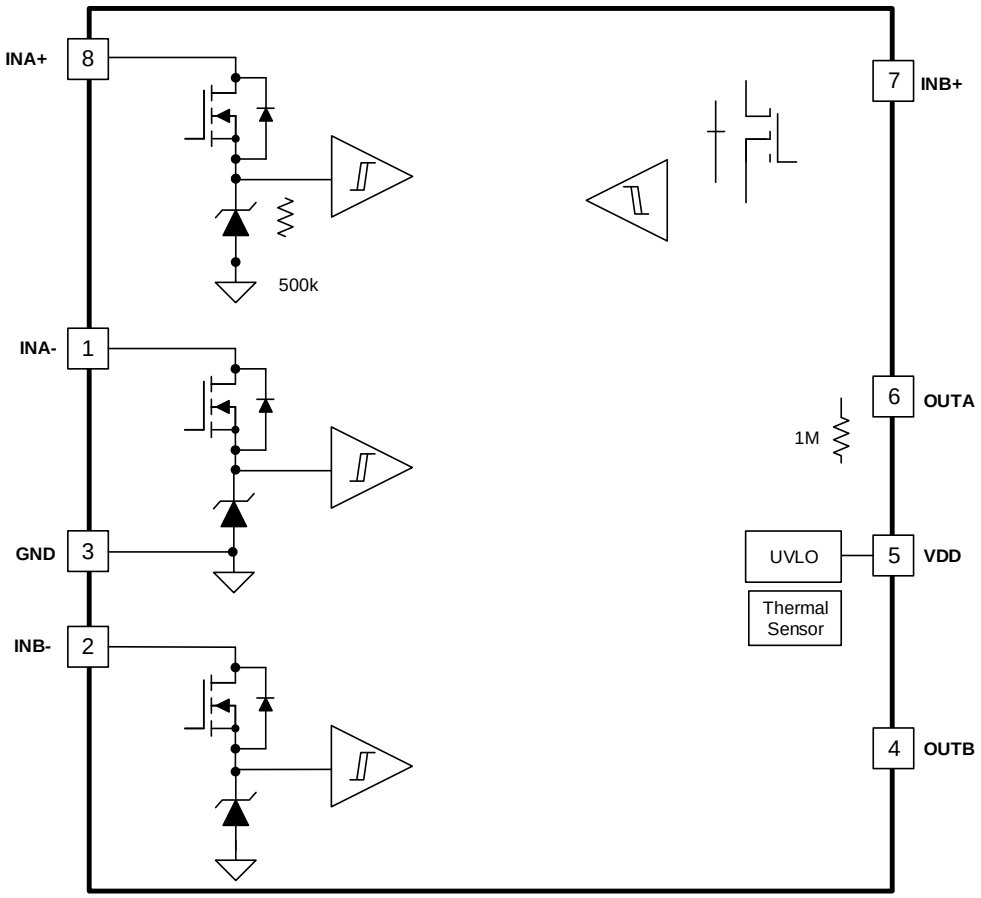


Figure 10. Operation Supply Current vs Frequency, C_{OUT}=1nF



Overview

The SCT52246 is a dual-channel non-invertible high-speed low side driver with supporting up to 24V wide supply for both power MOSFET and

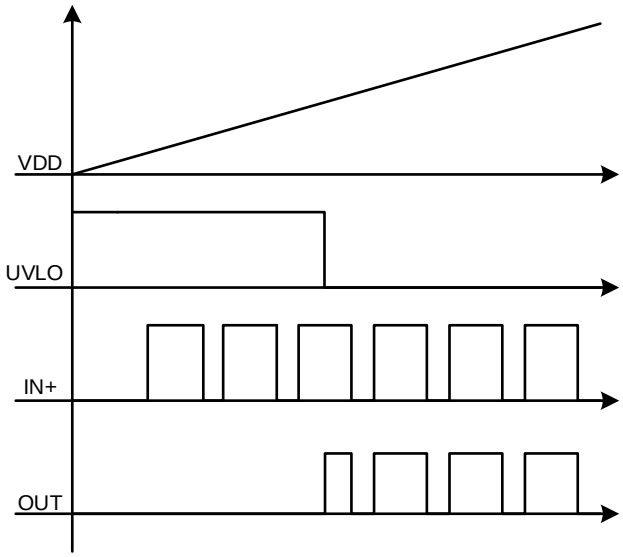


Figure 11. SCT52246 Output Vs VDD

Input Stage

The input of SCT52246 is compatible on TTL input-threshold logic that is independent of the VDD supply voltage. With typically high threshold = 2.1 V and typically low threshold = 1 V, the logic level thresholds are conveniently driven with PWM control signals derived from 3.3-V and 5-V digital power-controller devices. Wider hysteresis offers enhanced noise immunity compared to traditional TTL logic implementations, where the hysteresis is typically less than 0.5V. SCT52246 also features tight control of the input pin threshold voltage that ensures stable operation across temperature. The very low input parasitic capacitance on the input pins increases switching speed and reduces the propagation delay.

Output Stage

The SCT52246 output stage features the pull up structure with P-type MOSFET PM1 and N-type MOSFET NM1 in parallel, as shown in Figure 12. PM1 provides the pull up capability when OUT approaches VDD and the NM1 holds off state, which guarantees the driver output is up to VDD rail. The measurable on-resistance R_{OH} in steady state is the conduction resistance of PM1. NM1 provides a narrow instant peak sourcing current up to 4A to eliminate the turn on time and delay. During the output turn on transition, the equivalent hybrid pull on transient resistance is $1.5R_{OL}$, which is much lower than the DC measured R_{OH}.

The N-type MOSFET NM2 composes the output stage pull down structure; the R_{OL} is the DC measurement and represents the pull down impedance. The output stage of SCT52246 provides rail-to-rail operation, and is able to supply 4A sourcing and 4A sinking peak current. The presence of the MOSFET-body diodes also offers low impedance to switching overshoots and undershoots. The outputs of the dual channel drivers are designed to withstand 500-mA reverse current without either damaging the device or logic malfunction.

Figure 12. SCT52246 Output Stage

Thermal Shutdown

Once the junction temperature in the SCT52246 exceeds 170° C, the thermal sensing circuit stops switching until the junction temperature falling below 145° C, and the device restarts. Thermal shutdown prevents the damage on device during excessive heat and power dissipation condition.

Typical Application

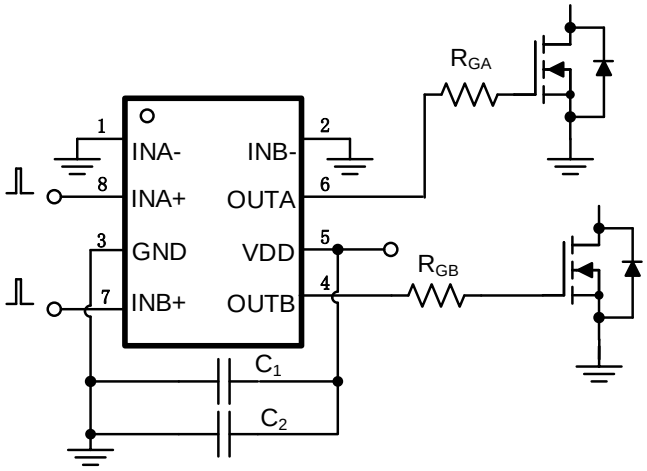


Figure 13. Dual Channel Driver Typical Application

Driver Power Dissipation

Generally, the power dissipated in the SCT52246 depends on the gate charge required of the power device (Qg), switching frequency, and use of external gate resistors. The SCT52246 features very low quiescent currents and internal logic to eliminate any shoot-through in the output driver stage, their effect on the power dissipation within the gate driver is negligible.

For the pure capacitive load, the power loss of each channel in SCT52246 is:

(1)

Where

- V_{DD} is supply voltage
- C_{Load} is the output capacitance
- F_{SW} is the switching frequency

For the the switching load of power MOSFET, the power loss of each channel in the SCT52246 is shown in equation (2), where charging a capacitor is determined by using the equivalence $Q_g = C_{LOAD}V_{DD}$. The gate charge includes the effects of the input capacitance plus the added charge needed to swing the drain voltage of the power device as it switches between the ON and OFF states. Manufacturers provide specifications that provide the typical and maximum gate charge, in nC, to switch the device under specified conditions.

(2)

Where

- Q_g is the gate charge of the power device
- f_{SW} is the switching frequency
- V_{DD} is the supply voltage

If R_G applied between driver and gate of power device to slow down the power device transition, the power dissipation of the driver shows as below:

(3)

Where

- R_{OH} is the equivalent pull up resistance of SCT52246
- R_{OL} is the pull down resistance of SCT52246
- R_G is the gate resistance between driver output and gate of power device.

Application Waveforms

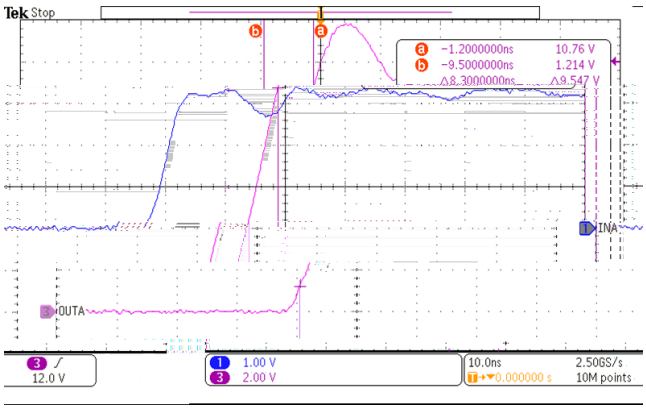


Figure 14. Driver INA+/INB+ Switching ON

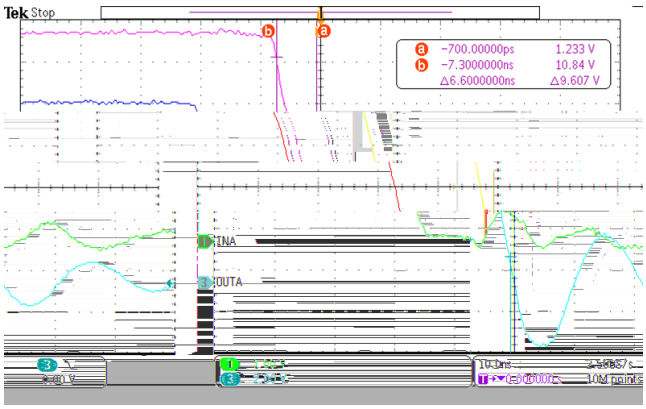


Figure 15. Driver INA+/INB+ Switching OFF

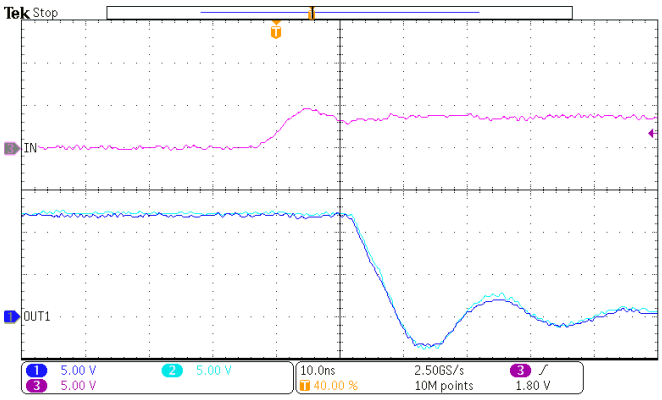


Figure 16. Driver INA-/INB- Switching OFF

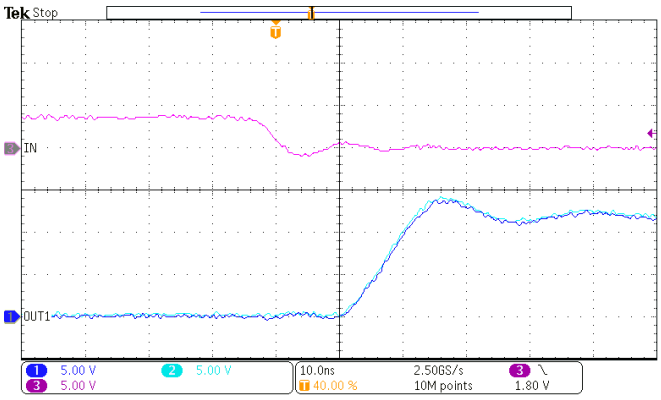


Figure 17. Driver INA-/INB- Switching ON

Layout Guideline

The SCT52246 provides the 4A output driving current and features very short rising and falling time at the power devices gate. The high di/dt causes driver output unexpected ringing when the driver output loop is not designed well. The regulator could suffer from malfunction and EMI noise problems if the power device gate has serious ringing. Below are the layout recommendations with using SCT52246 and Figure 18 is the layout example.

Put the SCT52246 as close as possible to the power device to minimize the gate driving loop including the driver output and power device gate. The power supply decoupling capacitors needs to be close to the VDD pin and GND pin to reduce the supply ripple. For the output stackable application, the driver input loop of two-channel input must be strictly symmetrical to ensure the input propagation delay is the same.

Star-point grounding is recommend to minimize noise coupling from one current loop to the other. The GND of the driver connects to the other circuit nodes such as source of power MOSFET or ground of PWM controller at single point. The connected paths must be as short as possible to reduce parasitic inductance. A ground plane is to provide noise shielding and thermal dissipation as well.

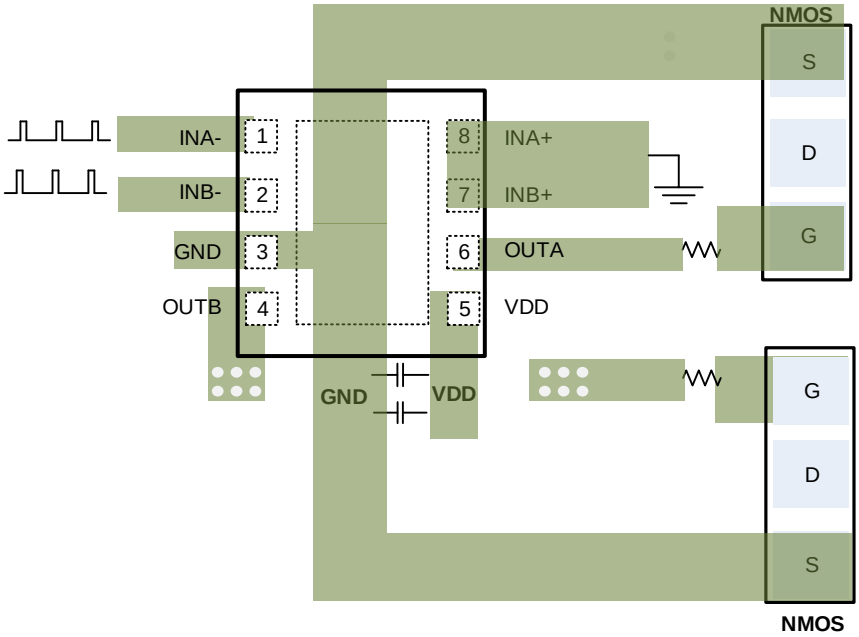


Figure 18. SCT52246 (Inverting Input) PCB Layout Example

Thermal Considerations

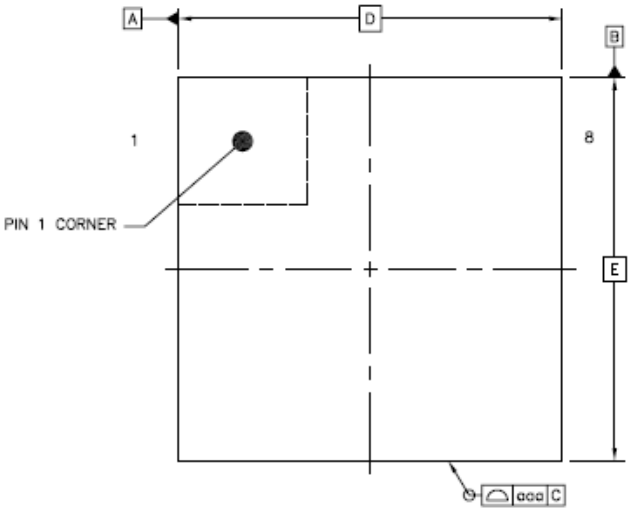
The maximum IC junction temperature should be restricted to 150°C under normal operating conditions. Calculate the maximum allowable dissipation, $P_{D(max)}$, and keep the actual power dissipation less than or equal to $P_{D(max)}$. The maximum-power-dissipation limit is determined using Equation (4).

(4)

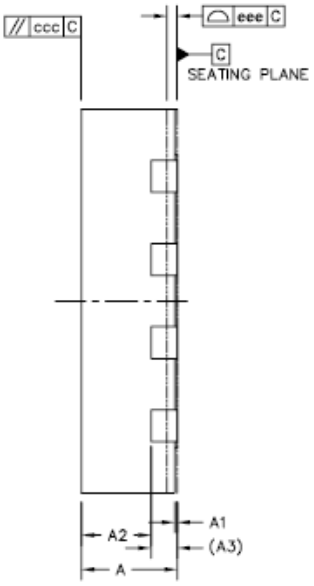
where

- T_A is the maximum ambient temperature for the application.
- R is the junction-to-ambient thermal resistance given in the Thermal Information table.

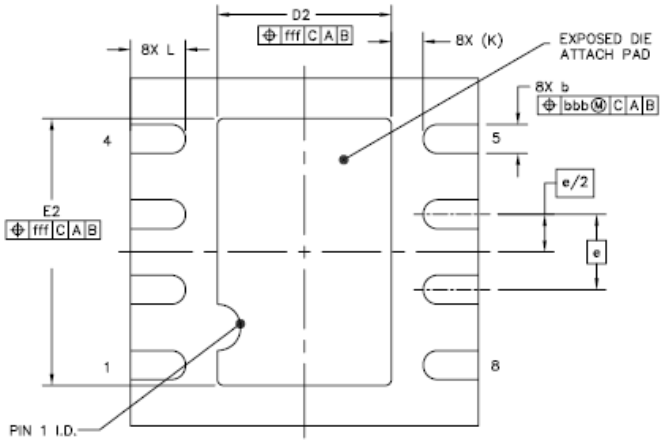
The real junction-to-ambient thermal resistance R of the package greatly depends on the PCB type, layout, and environmental factor. Soldering the ground pin to a large ground plate enhance the thermal performance. Using more vias connects the ground plate on the top layer and bottom layer around the IC without solder mask also improves the thermal capability.



TOP VIEW



BOTTOM VIEW

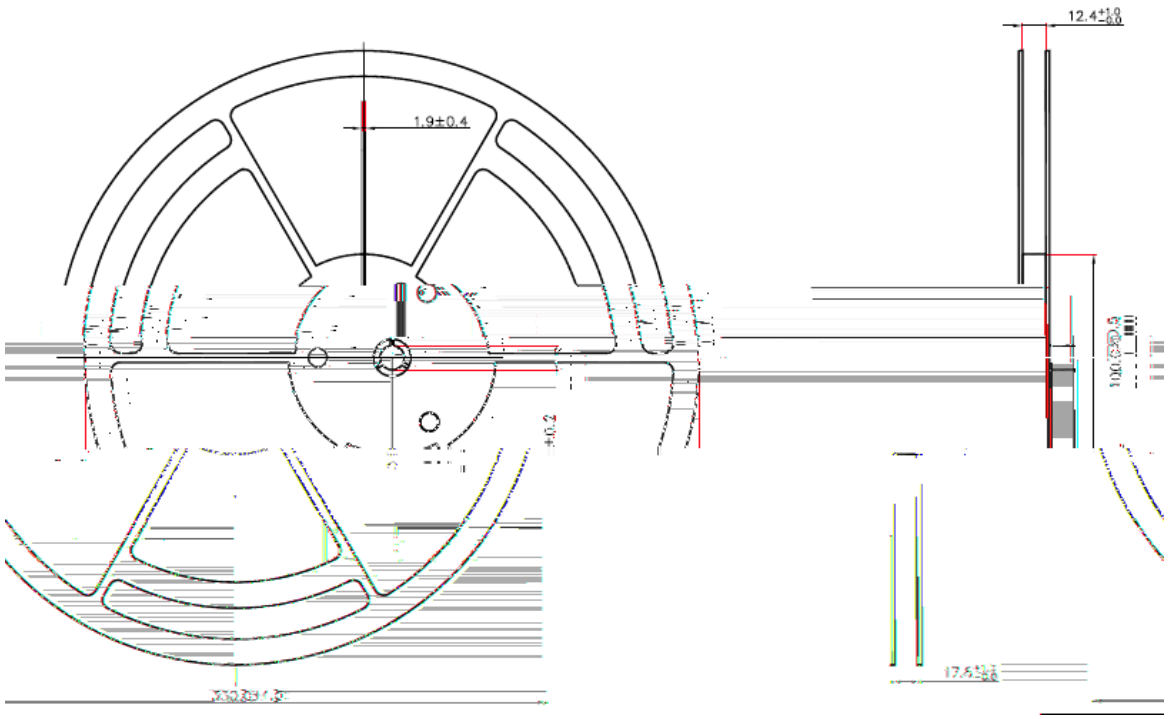


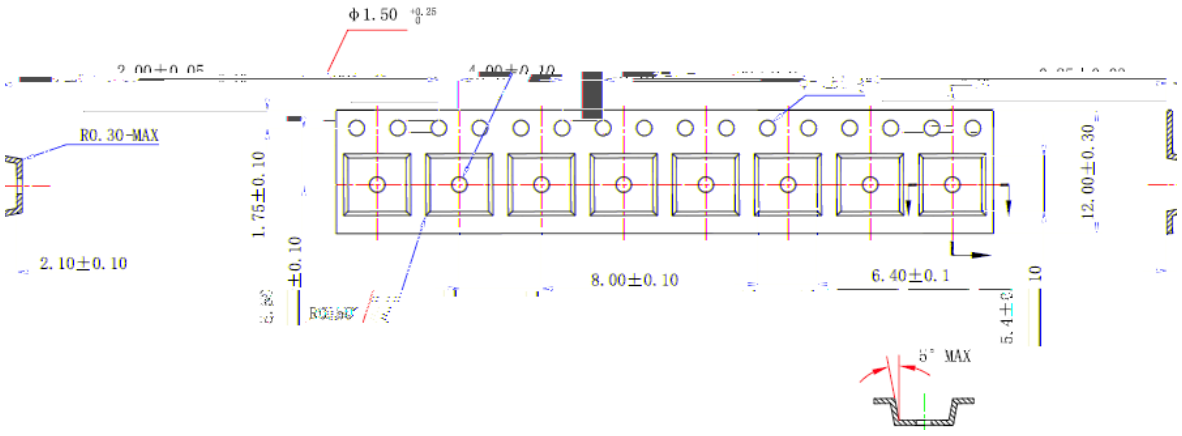
SIDE VIEW

SYMBOL	Unit: Millimeter		
	MIN	TYP	MAX
A	0.7	0.75	0.8
A1	0	0.02	0.05
A2	---	0.55	---
A3		0.203 REF	
b	0.2	0.25	0.3
D		3 BSC	
E		3 BSC	
e		0.65 BSC	
D2	1.45	1.5	1.55
E2	2.25	2.3	2.35
L	0.375	0.475	0.575
K		0.275 REF	
aaa		0.05	
ccc		0.1	
eee		0.08	
bbb		0.1	
fff		0.1	

NOTE:

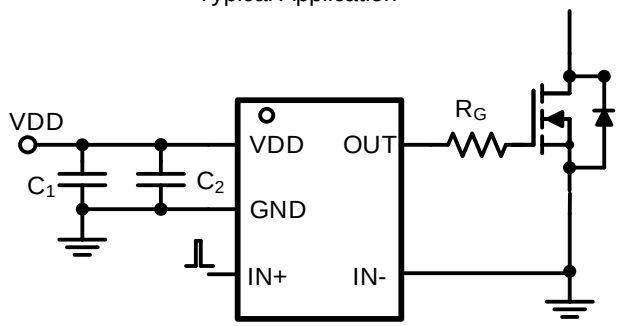
1. Drawing proposed to be made a JEDEC package outline MO-220 variation.
2. Drawing not to scale.
3. All linear dimensions are in millimeters.
4. Thermal pad shall be soldered on the board.
5. Dimensions of exposed pad on bottom of package do not include mold flash.
6. Contact PCB board fabrication for minimum solder mask web tolerances between the pins.





Feeding Direction

Single Channel, Non-Inverting MOSFET Gate Drive Typical Application



Typical Application Waveform

PART NUMBERS	DESCRIPTION	COMMENT(DE)(S)-(CRIP)(T)-